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U.S. PATENT DOCUMENTS

NUMBER ITAL.	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
AA		5,906,680	5/25/1999	Meyerson			
AB		6,190,375	2/2001	Kubo et al.			
AD		5,693,934	11/1997	Candelaria et al.			
AF		6,306,211	10/2001	Takabashi et al.			

U.S. PATENT APPLICATION PUBLICATIONS

NUMBER ITAL.	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
AC		2002/0160605	10/2002	Kanzawa et al.			
AE		2002/0015085	2/2002	Huang et al.			

FOREIGN PATENT DOCUMENTS

NUMBER ITAL.	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

OTHER DOCUMENTS (Including Author, Title, Date, Periodic Pages, Etc.)

AG	E. Kasper et al. "Growth of 1D GaS SiGe-Heterostructure Transistor (HBT) Structures," Jpn. J. Appl. Phys., Vol. 33 Pt. 1, No. 4B, April 1994, pp2412-2418;
AH	H.J. Ooster et al. in the paper entitled "Carbon Based SiGe Heterojunction Bipolar Transistors for High Frequency Application," IEEE BCTM 7.1, 1999 pp. 109-116.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in compliance with MPEP Section 609; Draw Ees through citation if not in compliance and not considered. Include copy of this form with next communication to applicant.

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